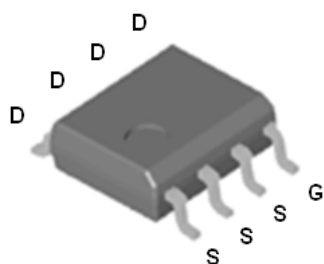


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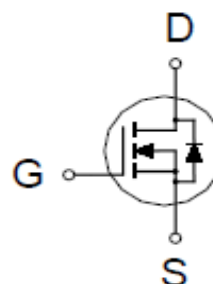
N-Channel Enhancement Mode MOSFET

PRODUCT SUMMARY

$V_{(BR)DSS}$	$R_{DS(ON)}$	I_D
100V	230mΩ @ $V_{GS} = 10V$	2.1A



SOP-8



ABSOLUTE MAXIMUM RATINGS ($T_A = 25\text{ }^{\circ}\text{C}$ Unless Otherwise Noted)

PARAMETERS/TEST CONDITIONS		SYMBOL	LIMITS	UNITS
Drain-Source Voltage		V_{DS}	100	V
Gate-Source Voltage		V_{GS}	±20	
Continuous Drain Current ¹	$T_A = 25\text{ }^{\circ}\text{C}$	I_D	2.1	A
	$T_A = 70\text{ }^{\circ}\text{C}$		1.7	
Pulsed Drain Current ²		I_{DM}	17	
Avalanche Current		I_{AS}	17	
Avalanche Energy	$L = 0.1\text{mH}$	E_{AS}	15.4	mJ
Power Dissipation	$T_A = 25\text{ }^{\circ}\text{C}$	P_D	2.3	W
	$T_A = 70\text{ }^{\circ}\text{C}$		1.5	
Junction & Storage Temperature Range		T_j, T_{stg}	-55 to 150	$^{\circ}\text{C}$

THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE	SYMBOL	TYPICAL	MAXIMUM	UNITS
Junction-to-Ambient	$R_{\theta JA}$		50	$^{\circ}\text{C} / \text{W}$
Junction-to-Case	$R_{\theta Jc}$		25	

¹Pulse width limited by maximum junction temperature.

²Limited by Package.

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ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$, Unless Otherwise Noted)

PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNITS
			MIN	TYP	MAX	
STATIC						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	100			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	1	1.5	2	
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0V, V_{GS} = \pm 20V$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 80V, V_{GS} = 0V$			1	μA
		$V_{DS} = 80V, V_{GS} = 0V, T_J = 55\text{ }^{\circ}C$			10	
Drain-Source On-State Resistance ¹	$R_{DS(ON)}$	$V_{GS} = 5V, I_D = 1A$		189	240	mΩ
		$V_{GS} = 10V, I_D = 2A$		182	230	
Forward Transconductance ¹	g_{fs}	$V_{DS} = 5V, I_D = 2A$		8		S
DYNAMIC						
Input Capacitance	C_{iss}	$V_{GS} = 0V, V_{DS} = 25V, f = 1MHz$		765		pF
Output Capacitance	C_{oss}			59		
Reverse Transfer Capacitance	C_{rss}			33		
Gate Resistance	R_g	$V_{GS} = 0V, V_{DS} = 0V, f = 1MHz$		1.85		Ω
Total Gate Charge ²	Q_g	$V_{DS} = 50V,$ $I_D = 2A, V_{GS} = 10V$		16.1		nC
Gate-Source Charge ²	Q_{gs}			1.9		
Gate-Drain Charge ²	Q_{gd}			5		
Turn-On Delay Time ²	$t_{d(on)}$	$V_{DS} = 50V,$ $I_D \cong 2A, V_{GS} = 10V, R_{GEN} = 6\Omega$		10		nS
Rise Time ²	t_r			12		
Turn-Off Delay Time ²	$t_{d(off)}$			15		
Fall Time ²	t_f			15		
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (T _A = 25 °C)						
Continuous Current	I_S				1.8	A
Forward Voltage ¹	V_{SD}	$I_F = 2A, V_{GS} = 0V$			1.4	V
Diode Reverse Recovery Time	t_{rr}	$I_F = 2A, dl/dt = 100A / \mu S$		28.9		nS
Diode Reverse Recovery Charge	Q_{rr}			29		nC

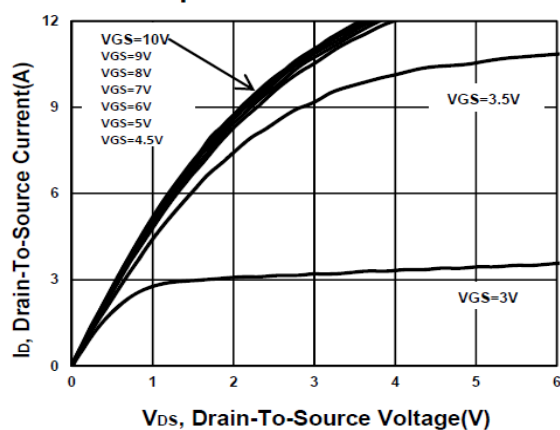
¹Pulse test : Pulse Width $\leq 300 \mu\text{sec}$, Duty Cycle $\leq 2\%$.

²Independent of operating temperature.

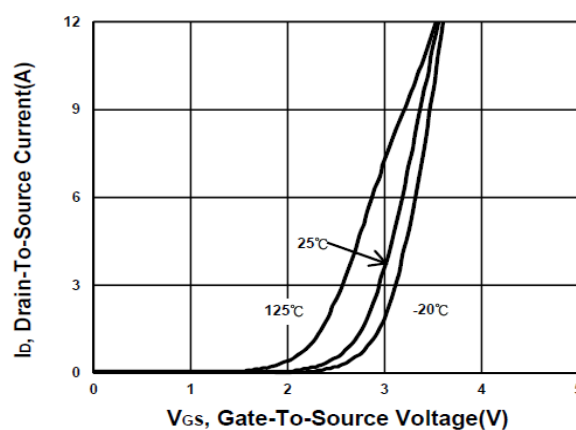
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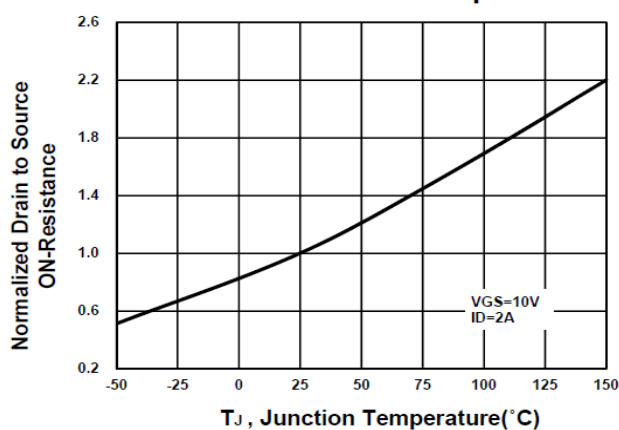
Output Characteristics



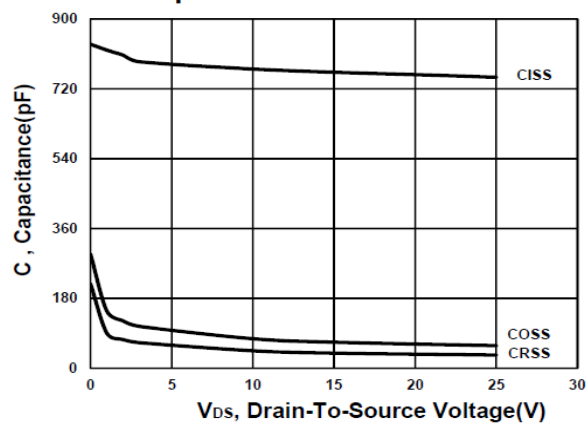
Transfer Characteristics



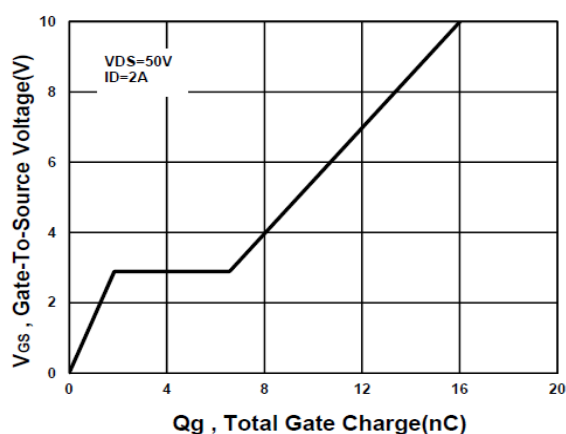
On-Resistance VS Temperature



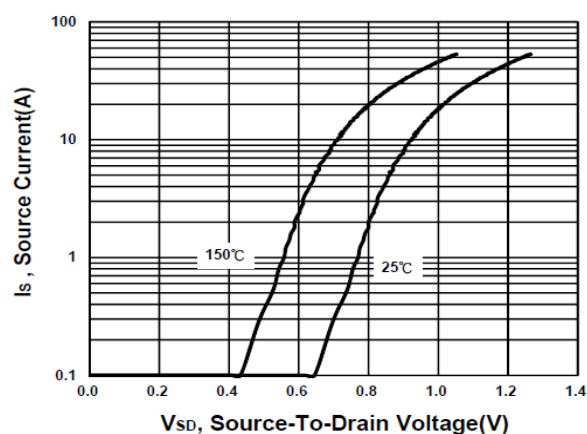
Capacitance Characteristic



Gate charge Characteristics



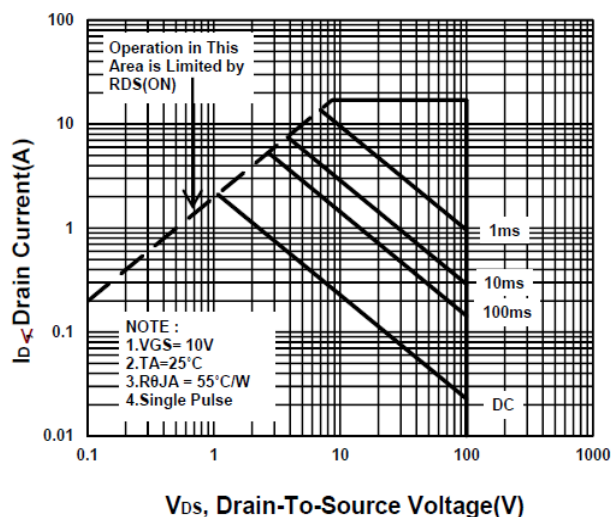
Source-Drain Diode Forward Voltage



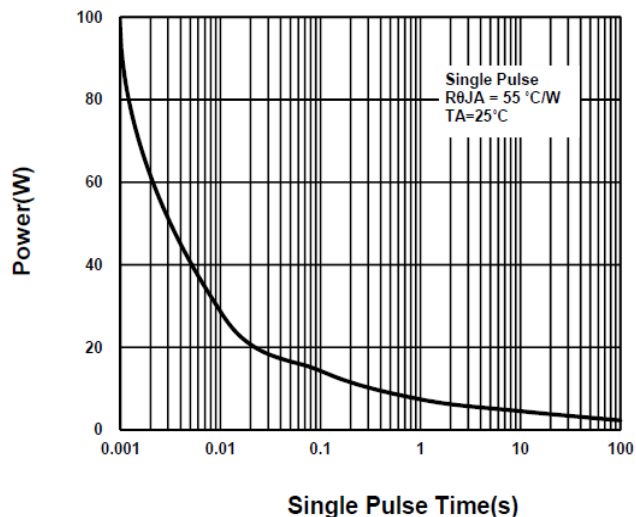
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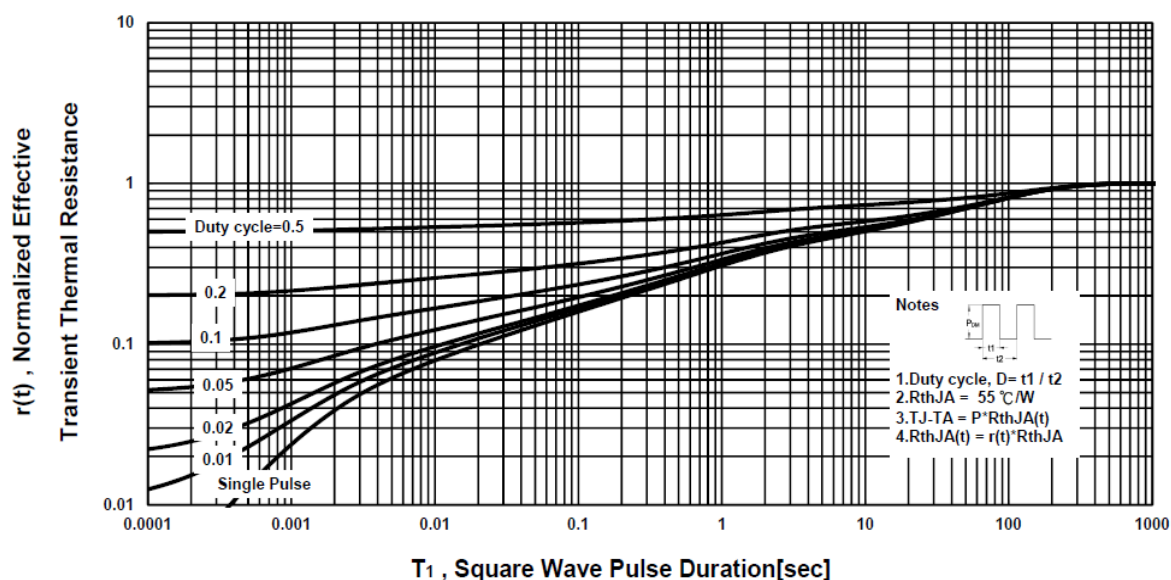
Safe Operating Area



Single Pulse Maximum Power Dissipation



Transient Thermal Response Curve



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Package Dimension

SOP-8 MECHANICAL DATA

Dimension	mm			Dimension	mm		
	Min.	Typ.	Max.		Min.	Typ.	Max.
A	4.8	4.9	5.0	H	0.4	0.6	0.93
B	3.8	3.9	4.0	I	0.19	0.21	0.25
C	5.79	6.0	6.2	J	0.25	0.375	0.5
D	0.33	0.4	0.51	K	0°	3°	18°
E	1.25	1.27	1.29				
F	1.1	1.3	1.65				
G	0.05	0.15	0.25				

